



Towards 100+ GHz Electronics

Ekaterina Laskin, Sorin Voinigescu

University of Toronto

CMOSET 2007

Friday July 13, 2007



Outline

- Motivation
- Applications above 100 GHz
- System architectures
- Circuit examples
 - 65nm CMOS
 - SiGe HBT
- Summary



Motivation

- Why 100+ GHz?
 - Silicon transistors can now operate above 100GHz
 - Better resolution for imagers ($\sim\lambda$)
 - Larger BW \rightarrow higher data rate
- Why CMOS / BiCMOS?
 - Can be integrated with signal processing
 - Integration of imaging arrays
 - Lower power
 - Lower system cost

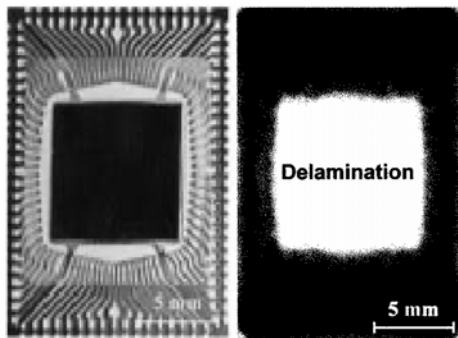


Applications above 100 GHz



Applications above 100 GHz

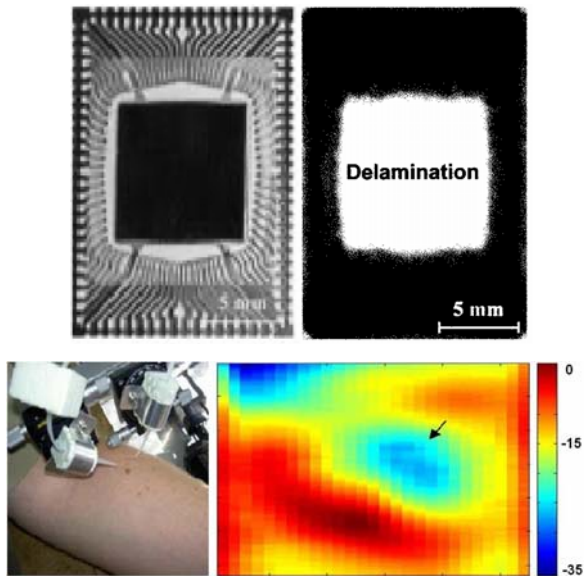
- Industrial





Applications above 100 GHz

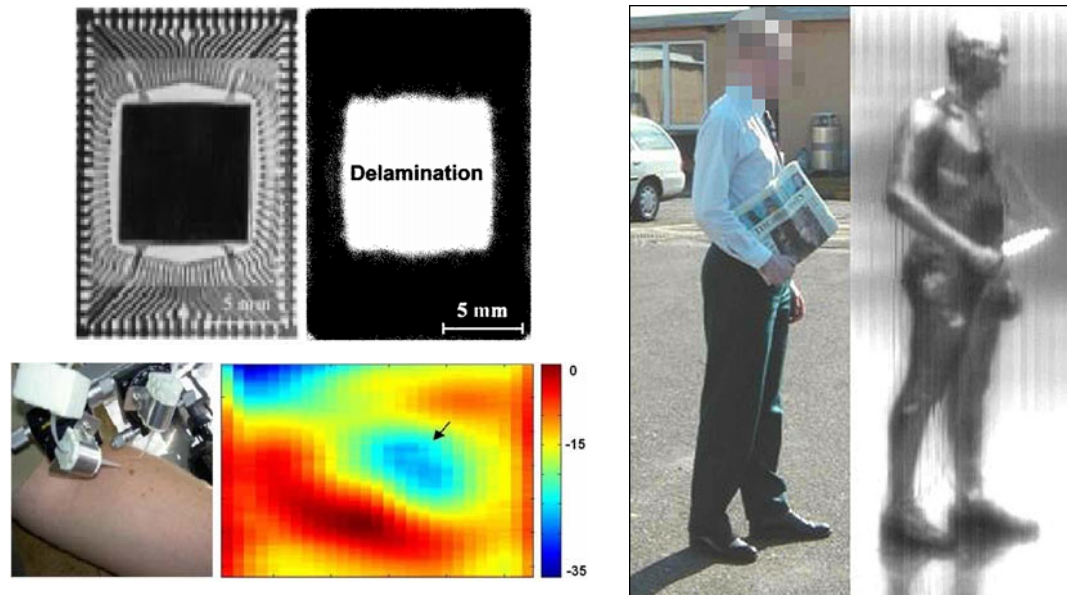
- Industrial, medical





Applications above 100 GHz

- Industrial, medical and security imagers





Applications above 100 GHz

- Industrial, medical and security imagers
- Possible radio astronomy applications
 - ALMA[†] band 3: 84 - 116 GHz [†] Atacama Large MM-Wave Array
 - ALMA band 4: 125 - 163 GHz





Applications above 100 GHz

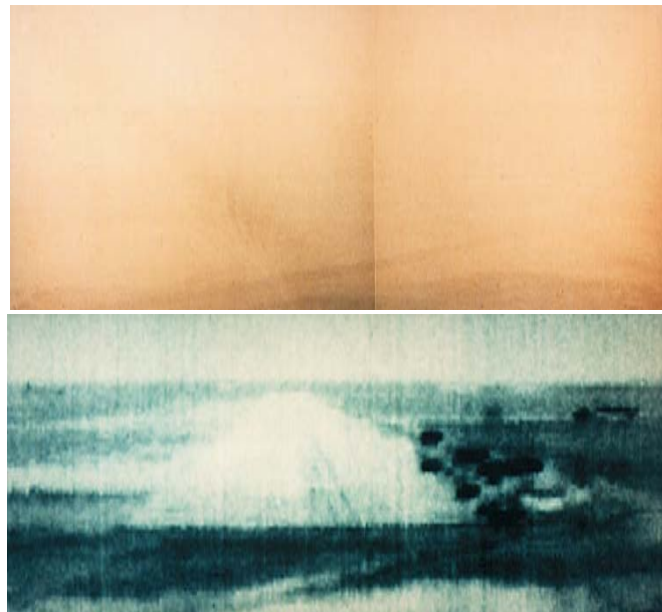
- Night- and fog-vision cameras





Applications above 100 GHz

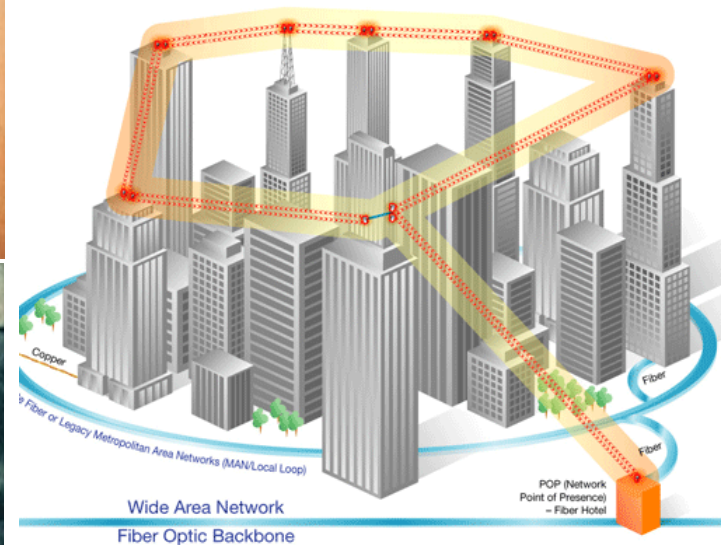
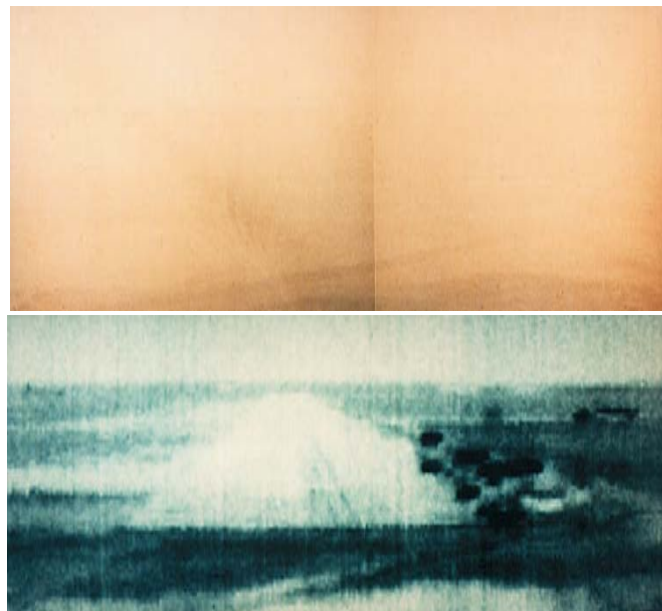
- Night- and fog-vision cameras





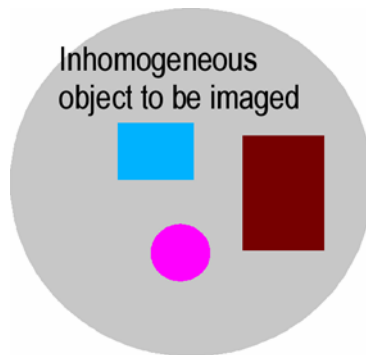
Applications above 100 GHz

- Night- and fog-vision cameras
- Wireless links with > 10 Gb/s data rate
 - Last mile, chip-to-chip



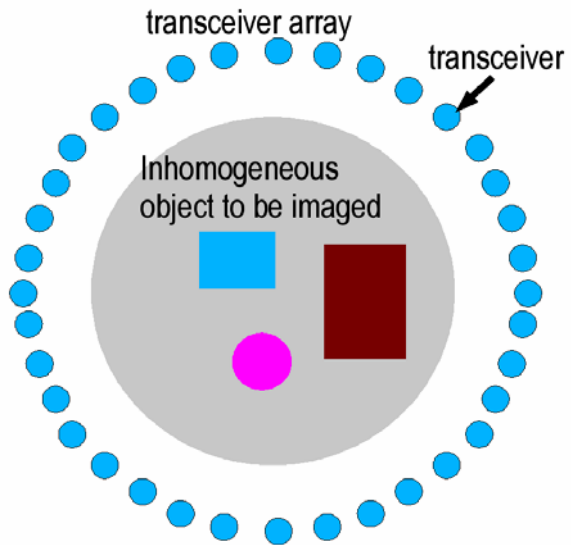


80-GHz Imaging Transceiver



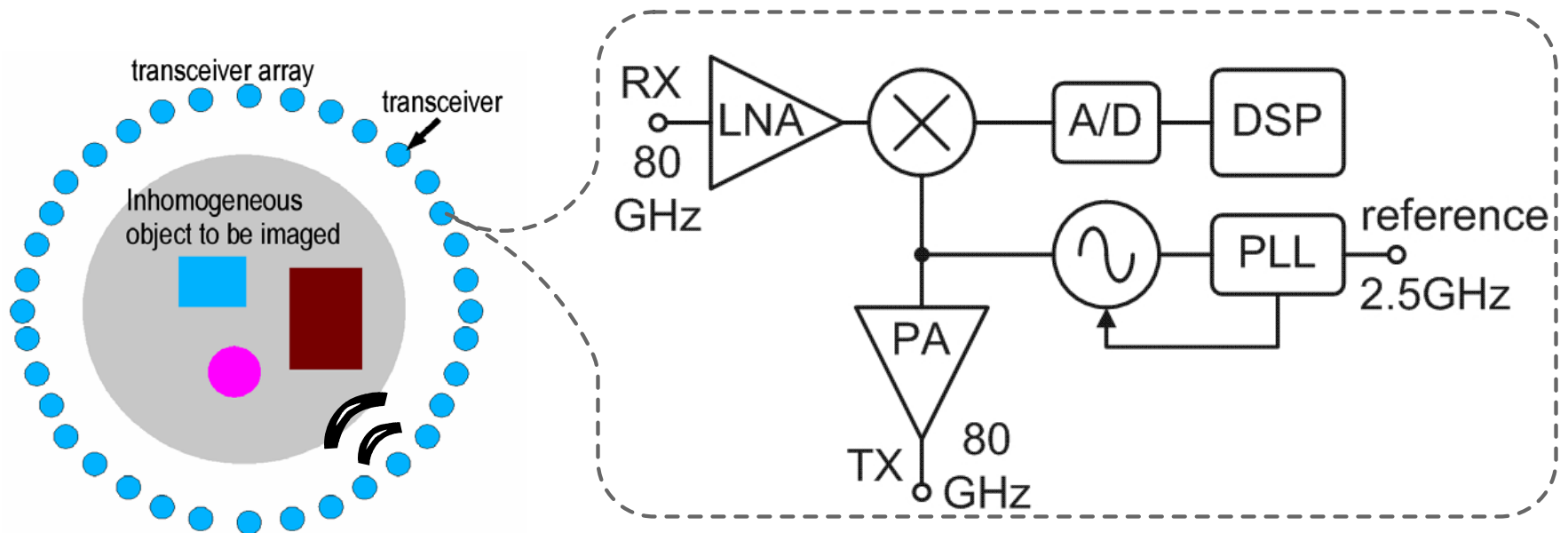


80-GHz Imaging Transceiver





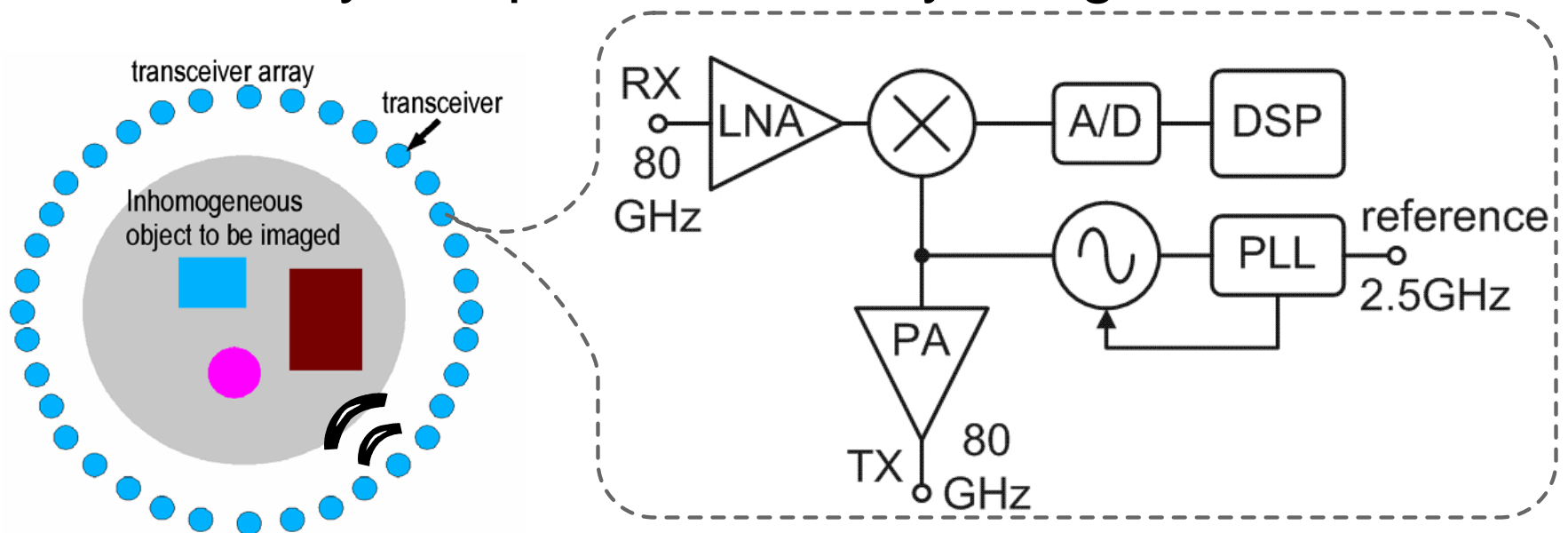
80-GHz Imaging Transceiver





80-GHz Imaging Transceiver

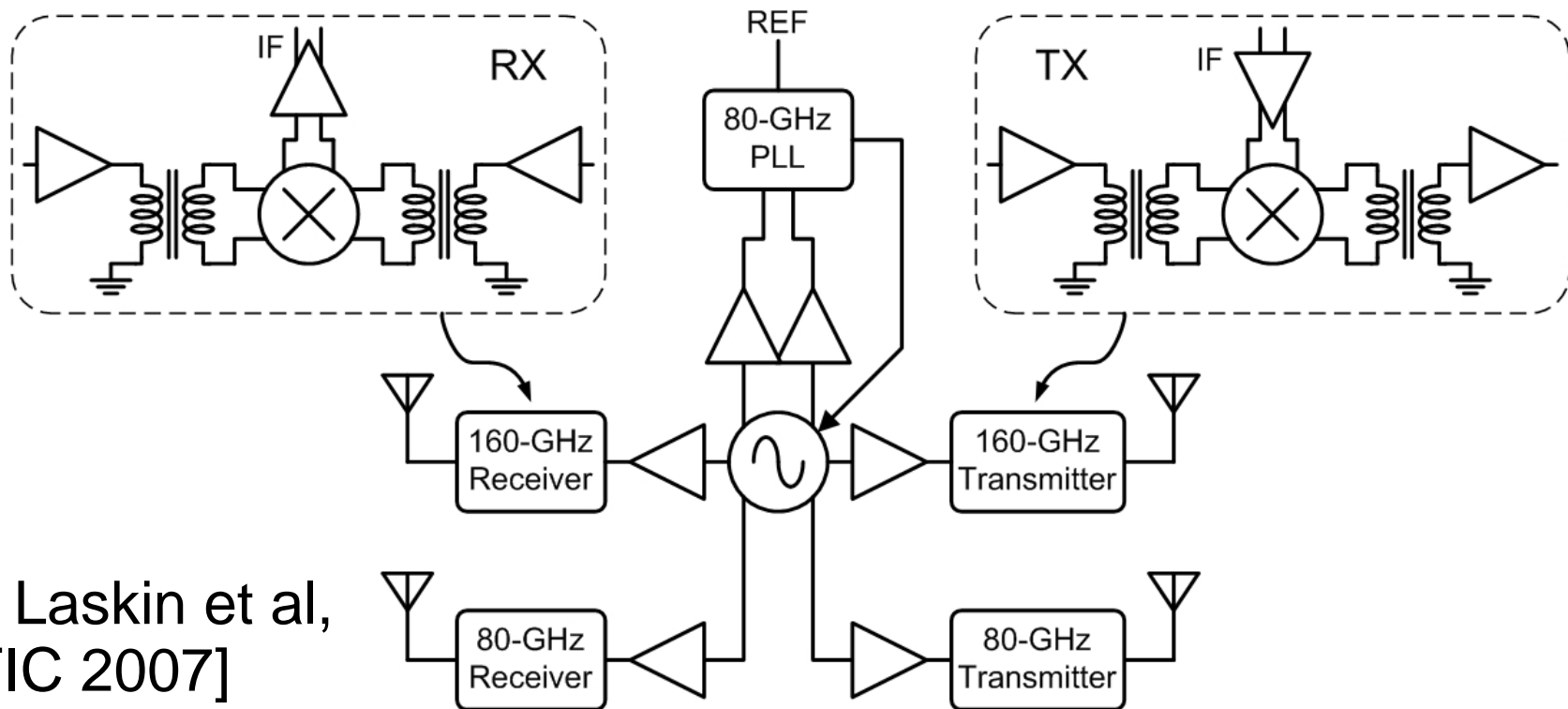
- Crosstalk suppression by system architecture
 - Different frequencies in TX and RX modes
 - One TX on, all other TXRX in receive mode
- Need very low power for array integration





80/160GHz Transceiver Array

- Save power using 1 multi-signal VCO+PLL
- VCO signal distribution using transformers

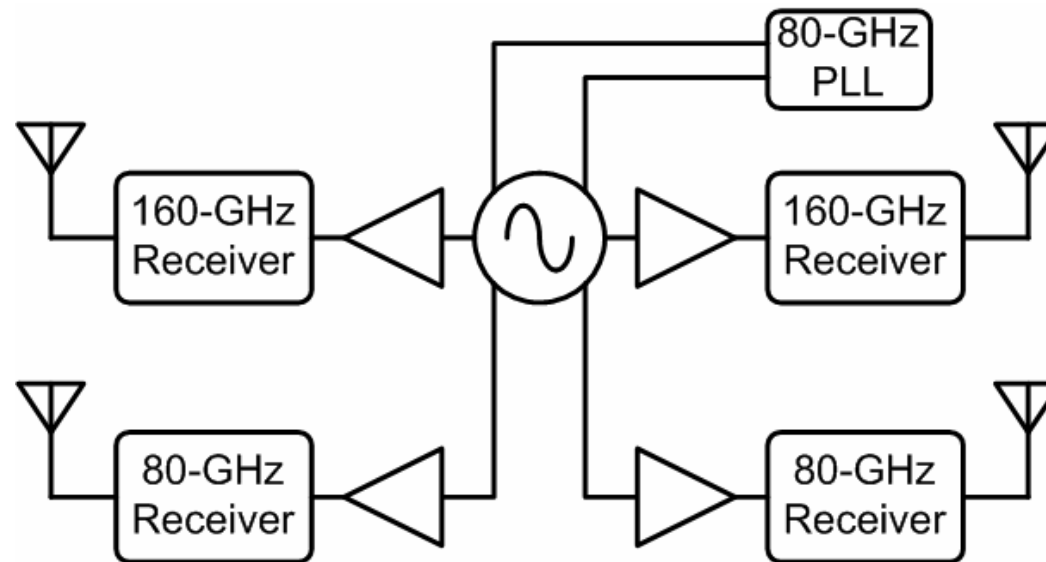


[E. Laskin et al,
RFIC 2007]



80/160-GHz Receiver Array

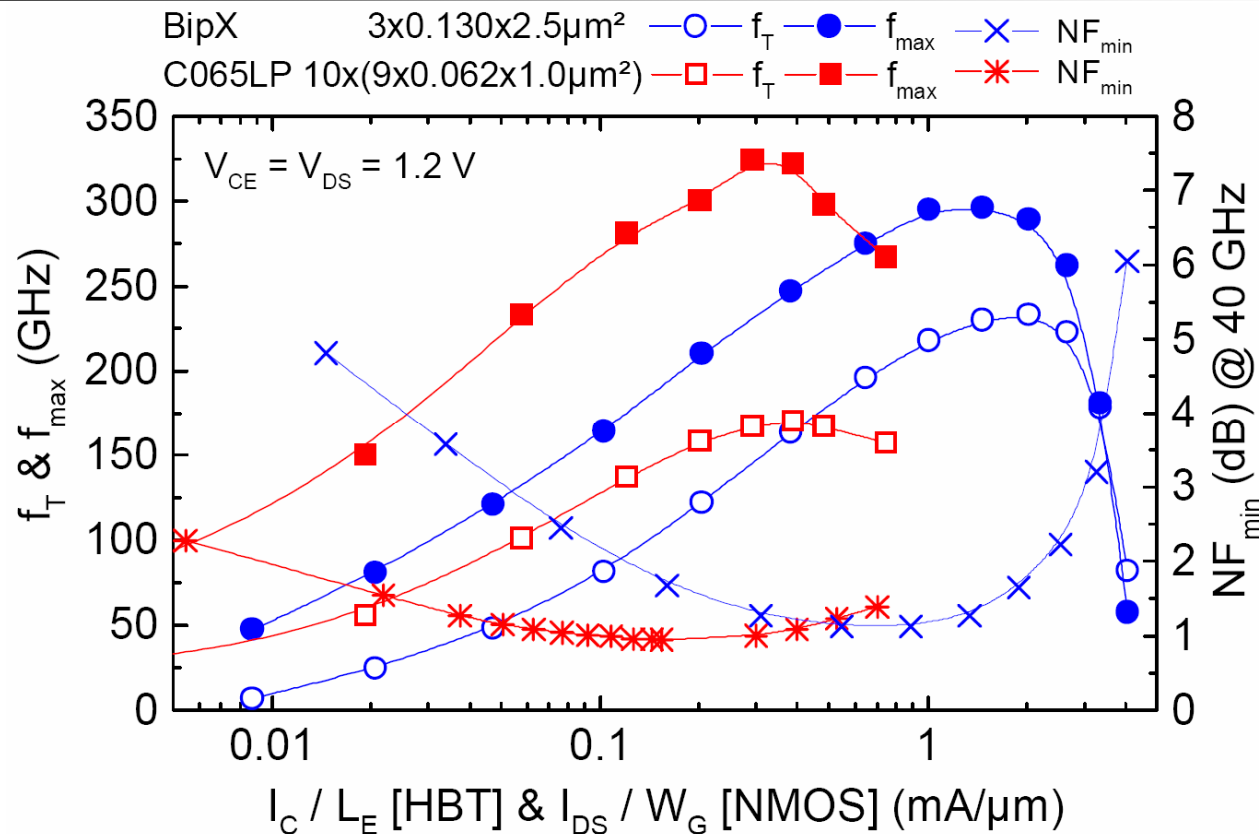
- Passive imaging receiver
- Suitable for implementation in CMOS



[74-94 GHz Receiver,
K. W. Tang, CICC 2007]



65nm NMOS vs. SiGe HBT



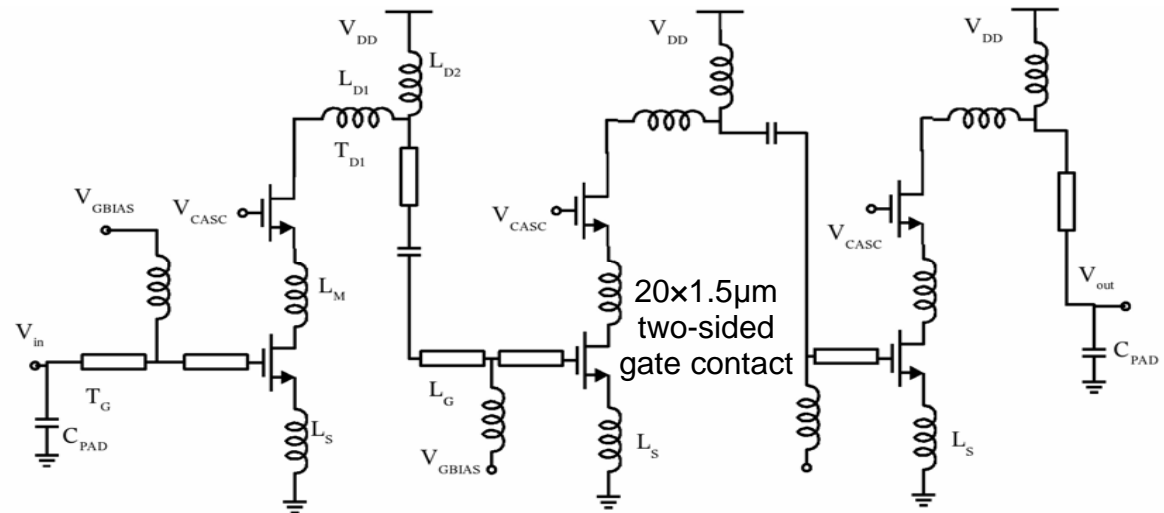
- Comparable high frequency performance

[P. Chevalier et al. CSICS-2006]



CMOS vs. HBT LNAs

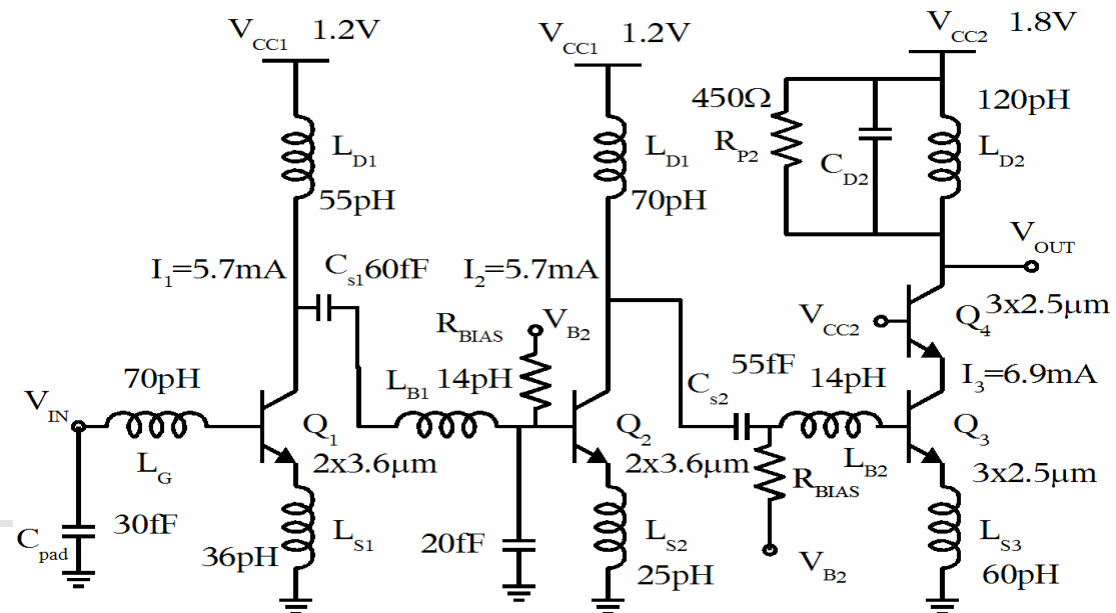
65nm CMOS
LNA
(55 mW)



290-GHz SiGe
HBT LNA
(52 mW)

[S.T. Nicolson et al.
IMS-07, CSICS-06]

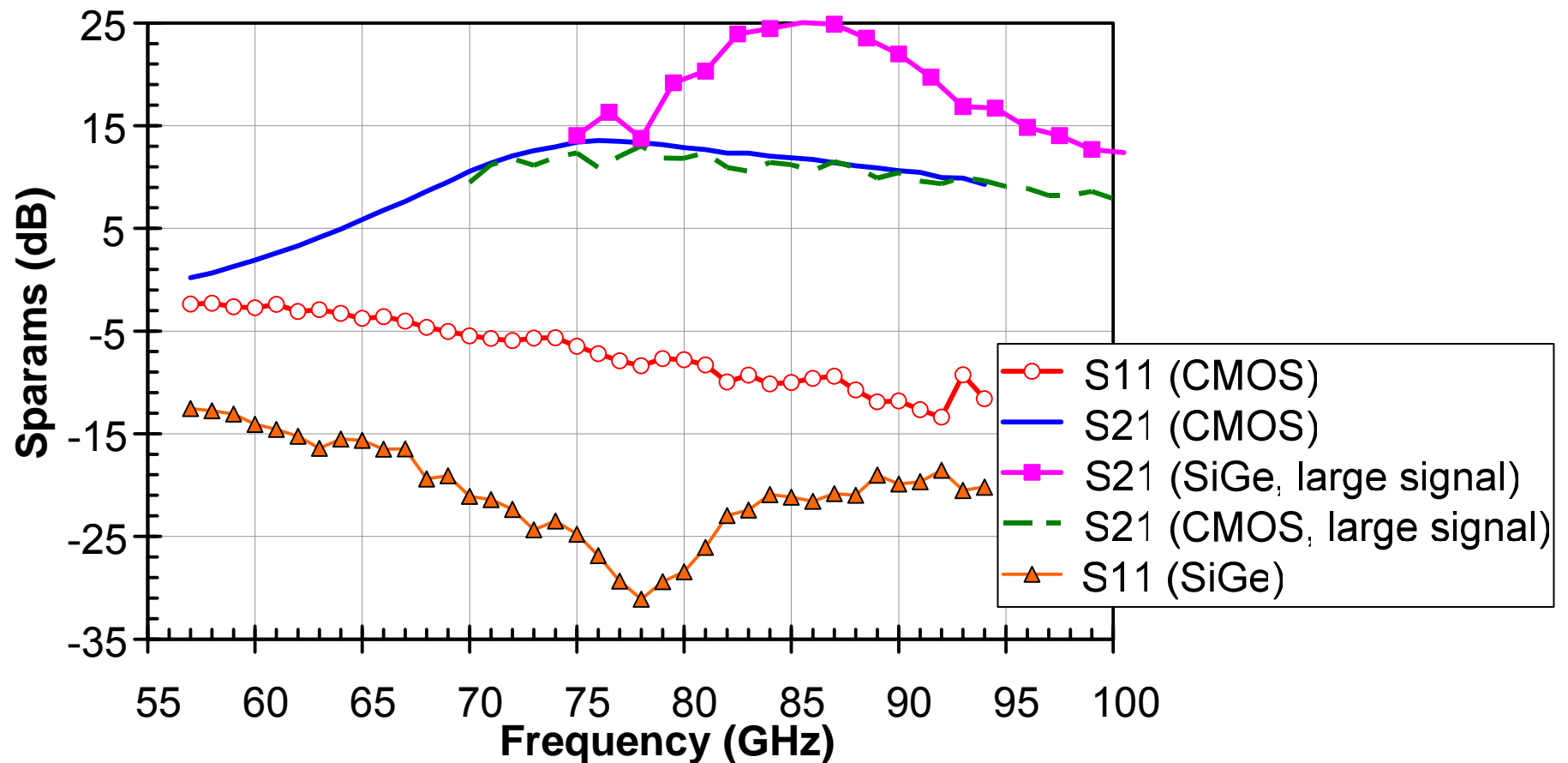
July 13, 2007





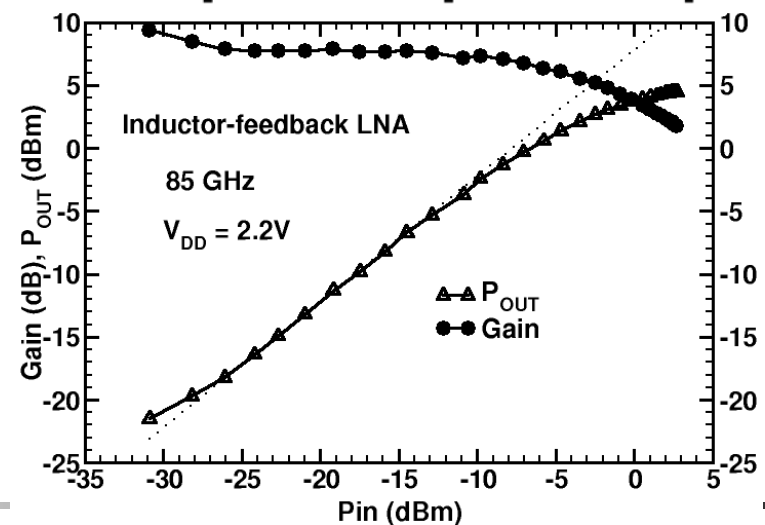
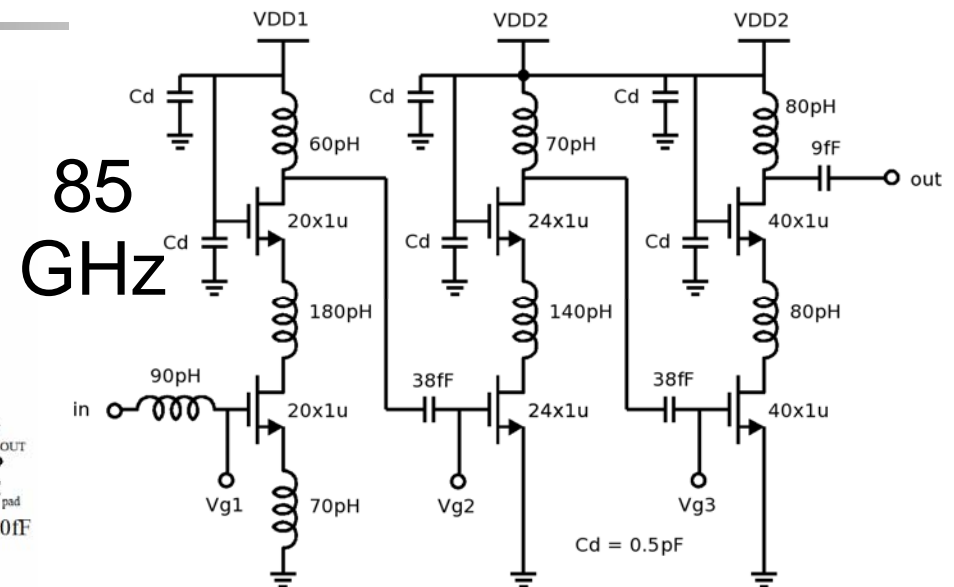
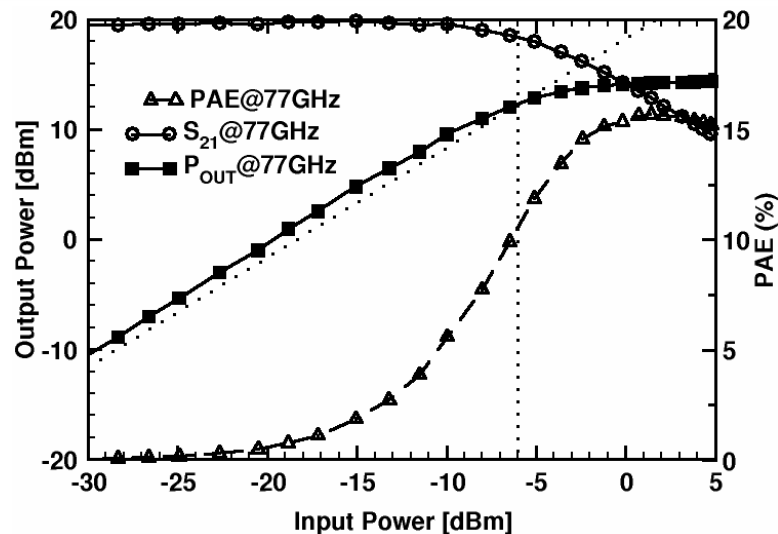
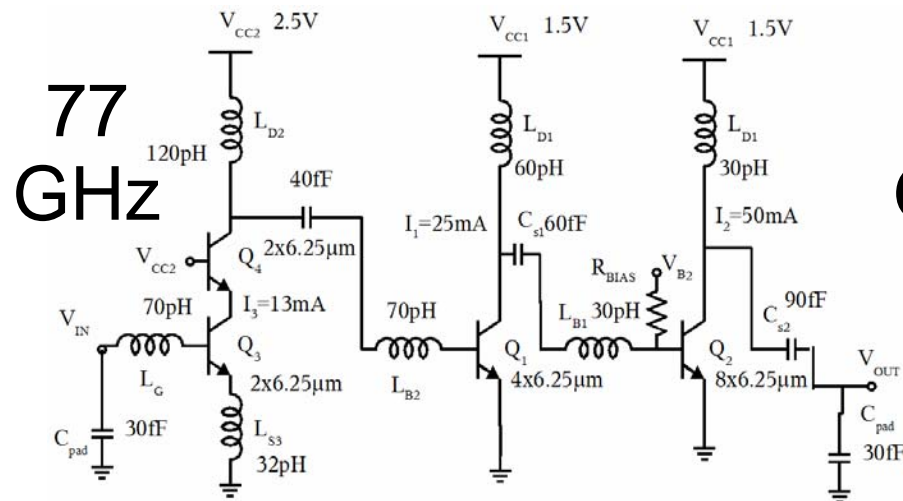
CMOS vs. HBT LNAs

- CMOS gain and output power is lower than SiGe



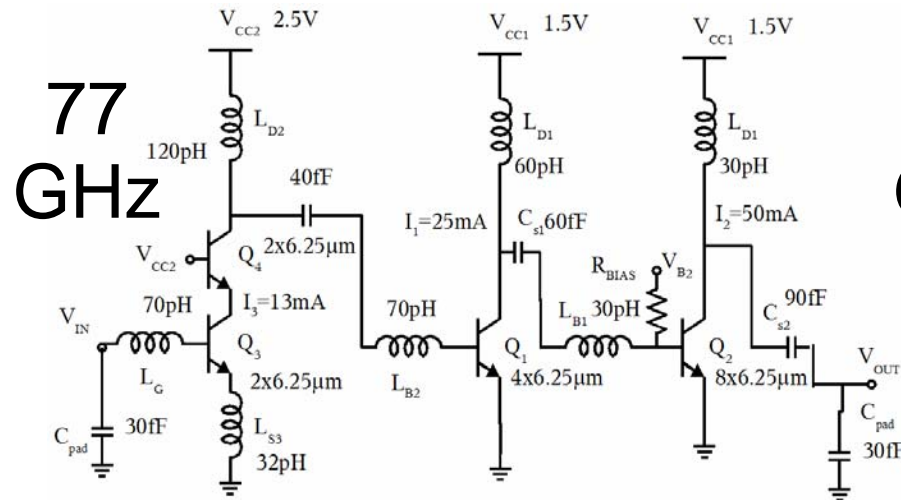


HBT vs. CMOS PAs

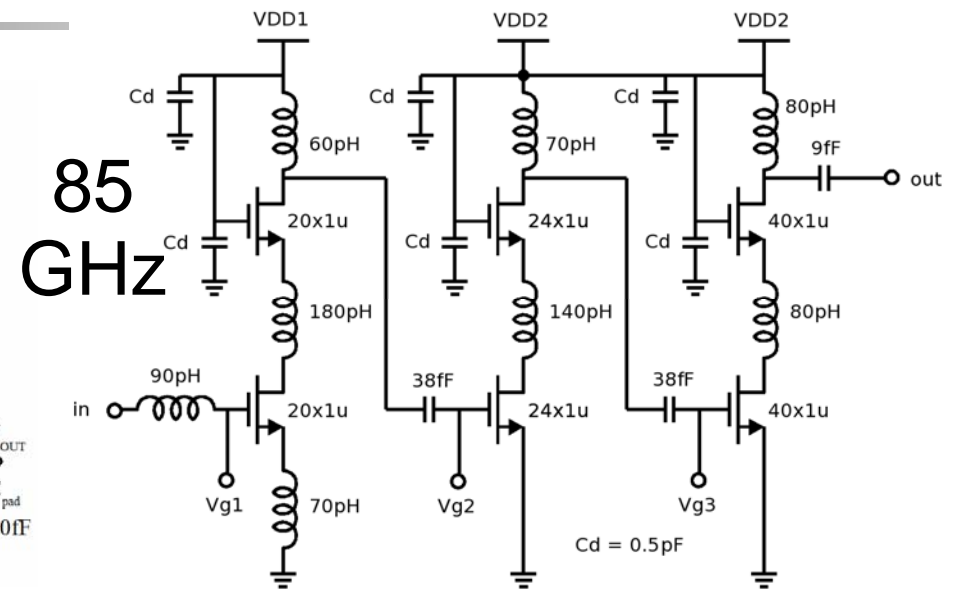




HBT vs. CMOS PAs



- $G = 19 \text{ dB}$
- $OP_{1\text{dB}} = 12 \text{ dBm}$
- $P_{\text{SAT}} = 14.6 \text{ dBm}$
- $PAE = 15.5\%$
- $P_{\text{DC}} = 161 \text{ mW}$

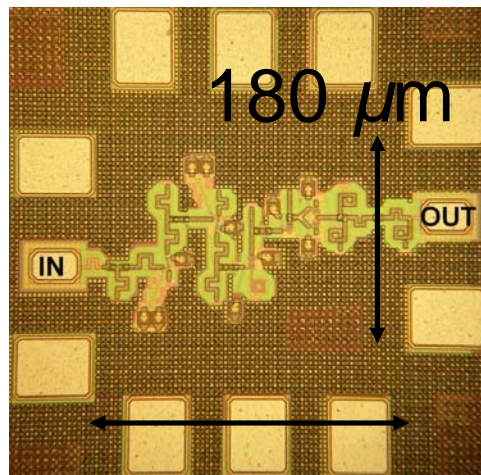


- $G = 7 \text{ dB}$
- $OP_{1\text{dB}} = -1 \text{ dBm}$
- $P_{\text{SAT}} = 5 \text{ dBm}$
- $P_{\text{DC}} = 55 \text{ mW}$

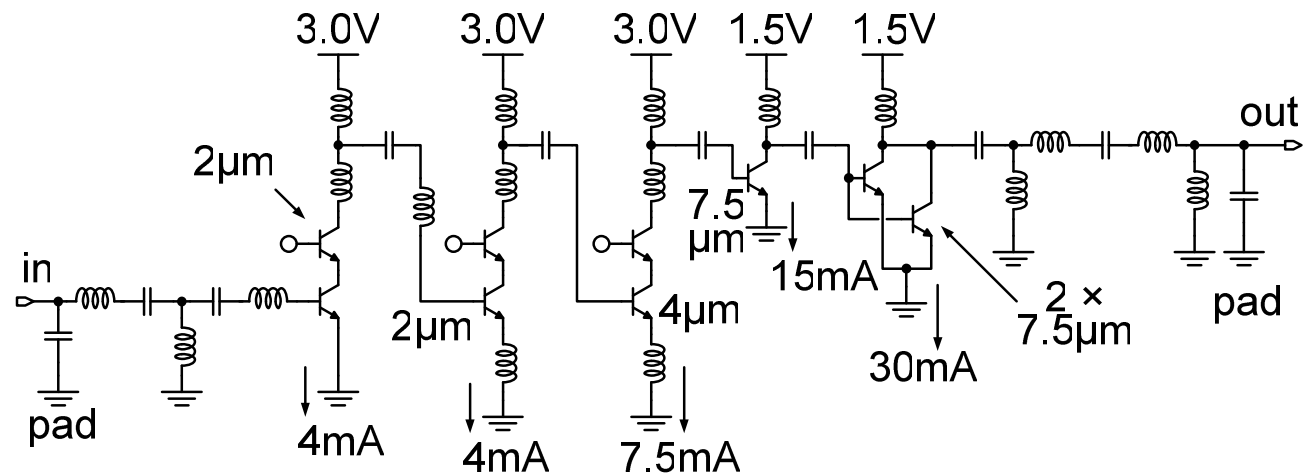


140-GHz Amplifier

- Cascodes \rightarrow gain, CE stages \rightarrow output power
- $R_E + R_B \approx 50\Omega \rightarrow$ No input degeneration
- Degeneration in 2nd stage for interstage matching
- Ratioed inductors, split loads for gain invariability
- Biased at peak- f_{MAX} for max power transfer

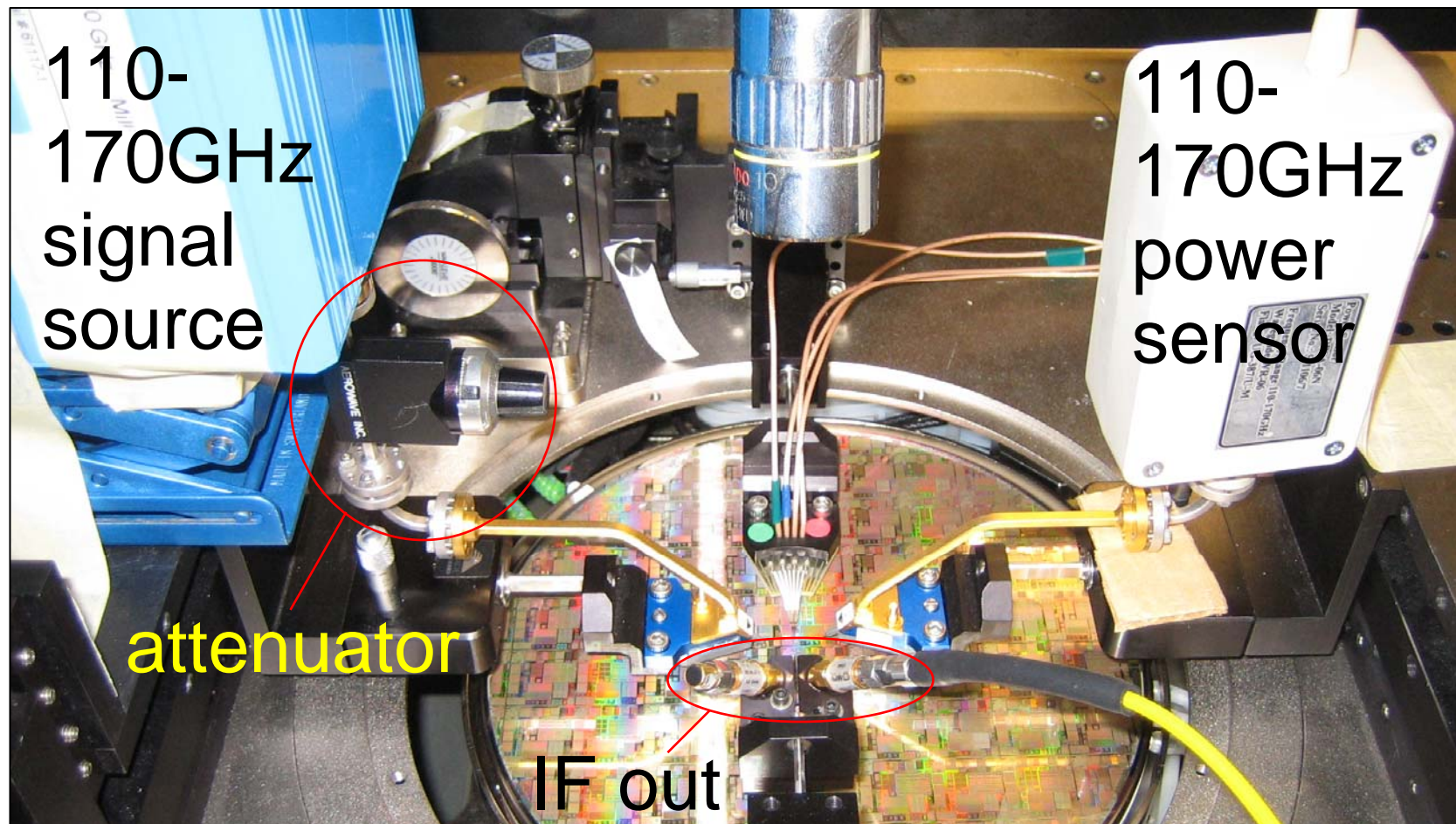


340 μm



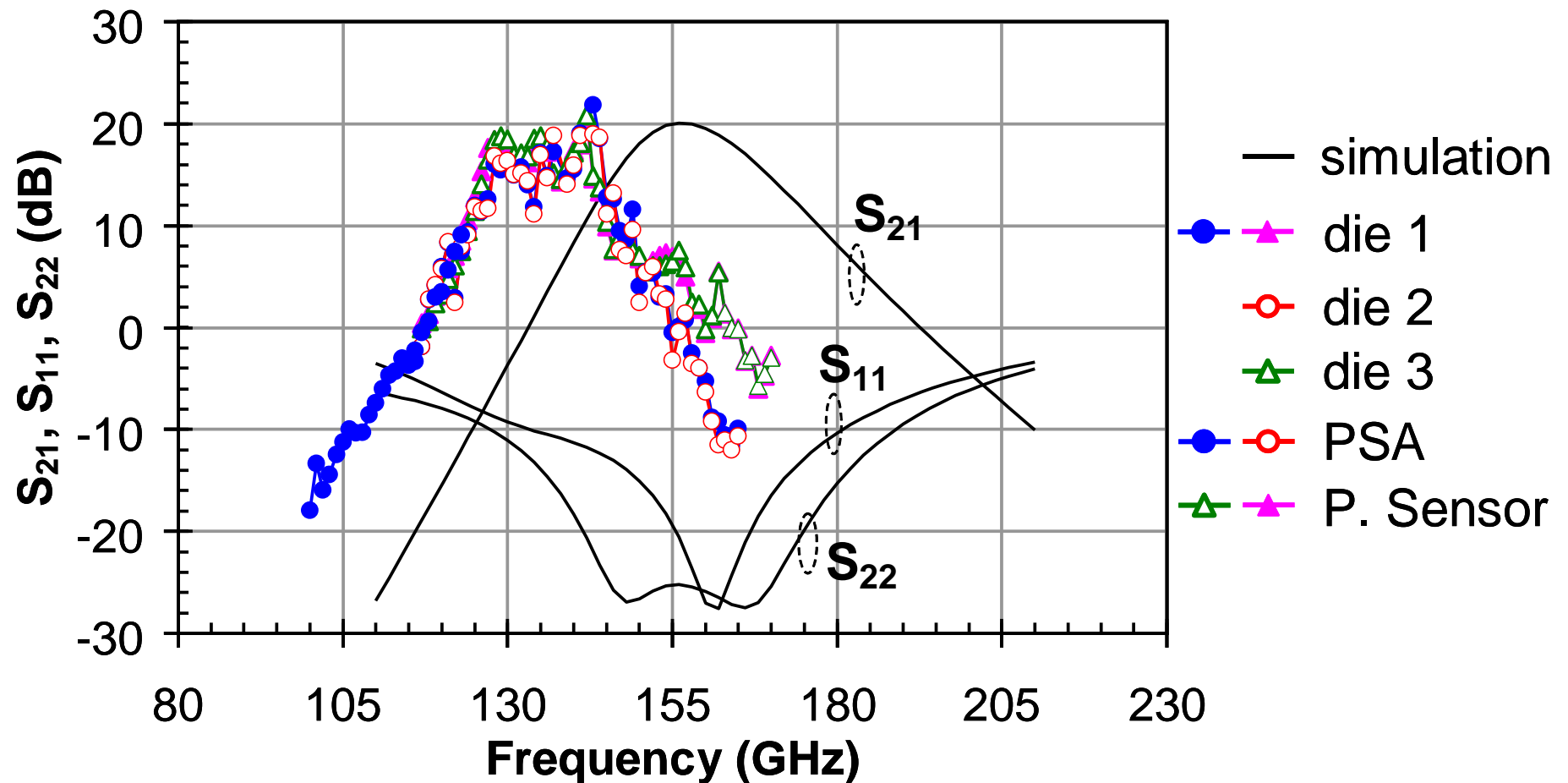


170-GHz Measurement Setup





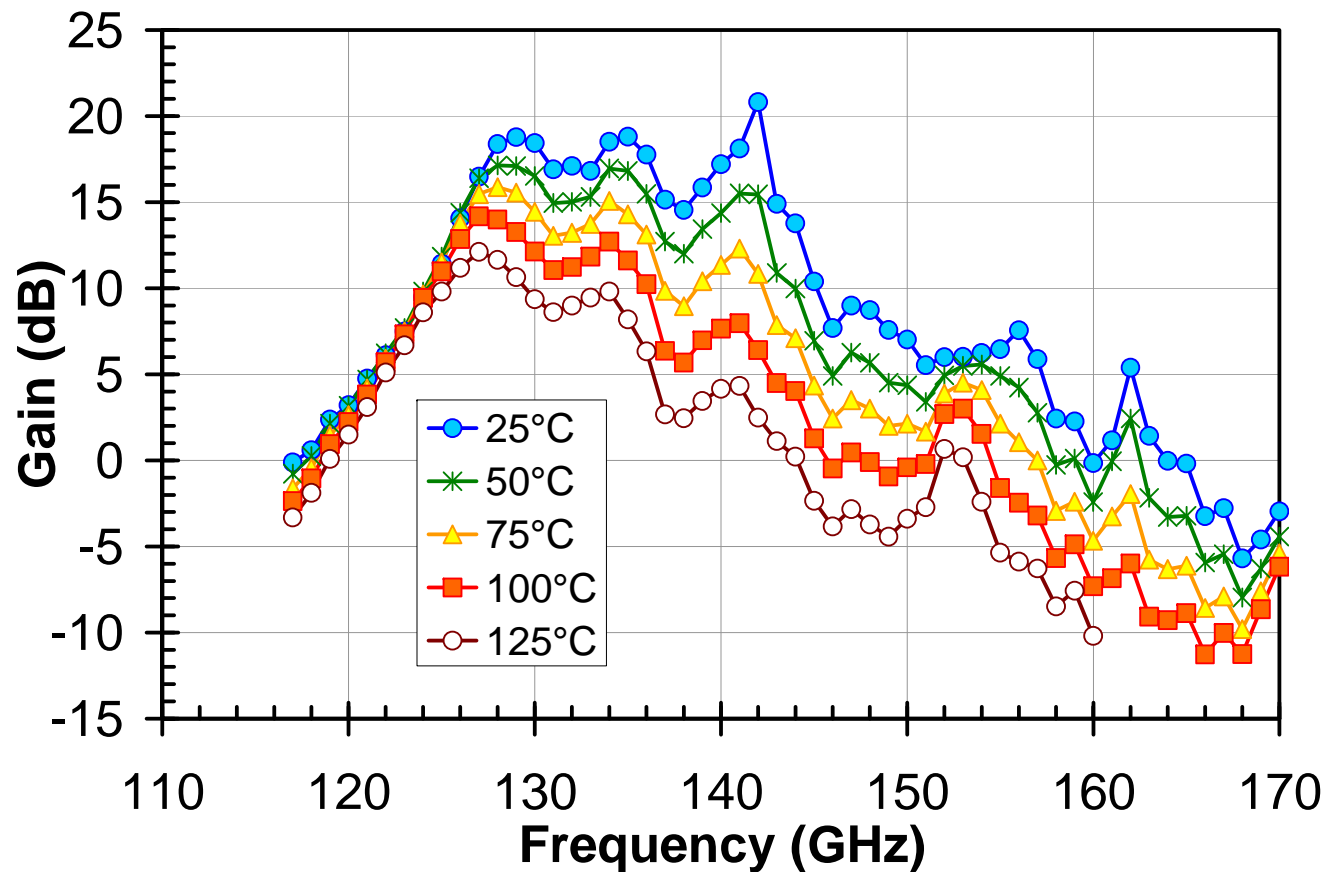
Amplifier - Measured vs. Sim





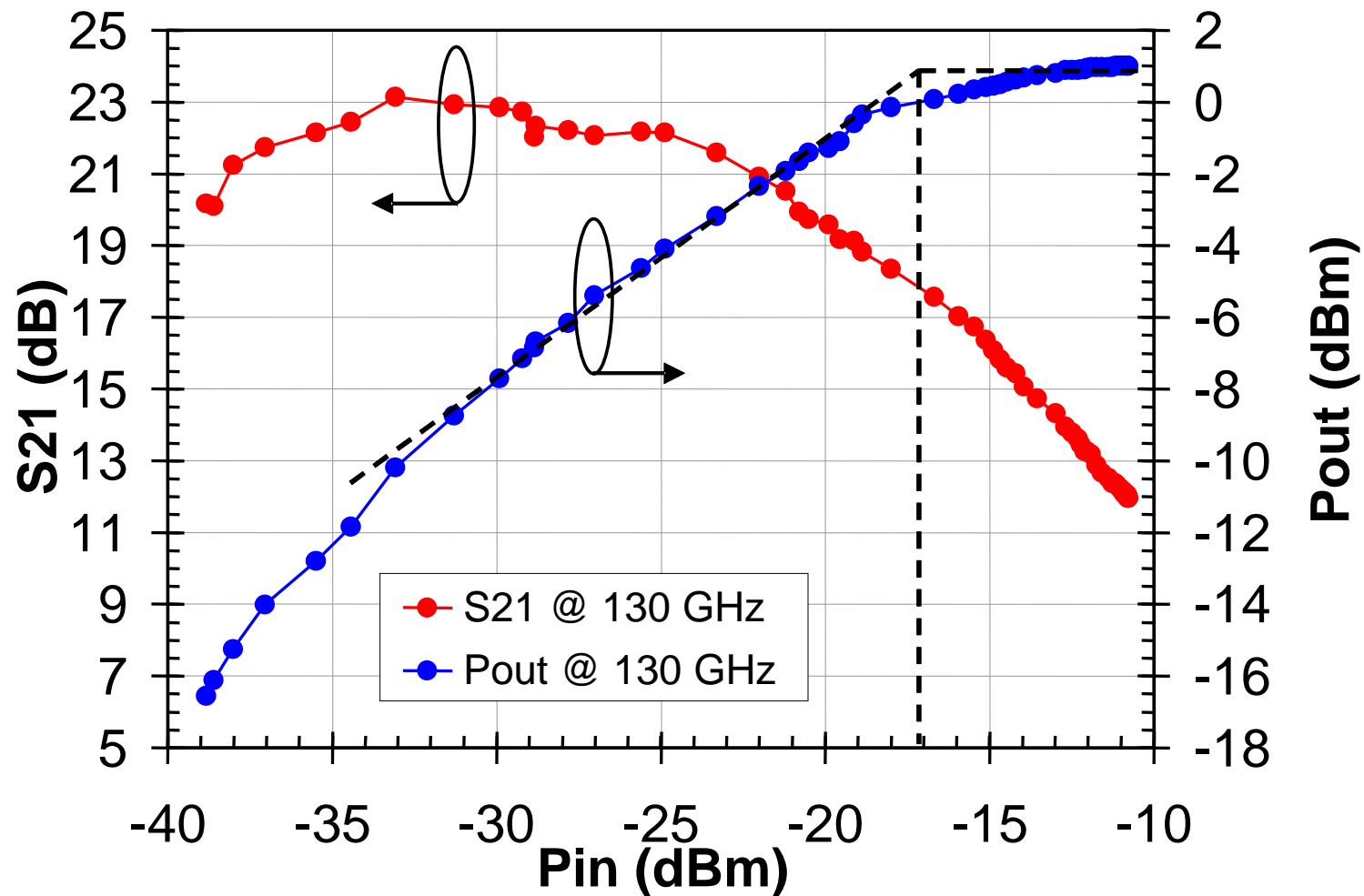
Amplifier Over Temperature

- Nominal wafer, measured using power sensor





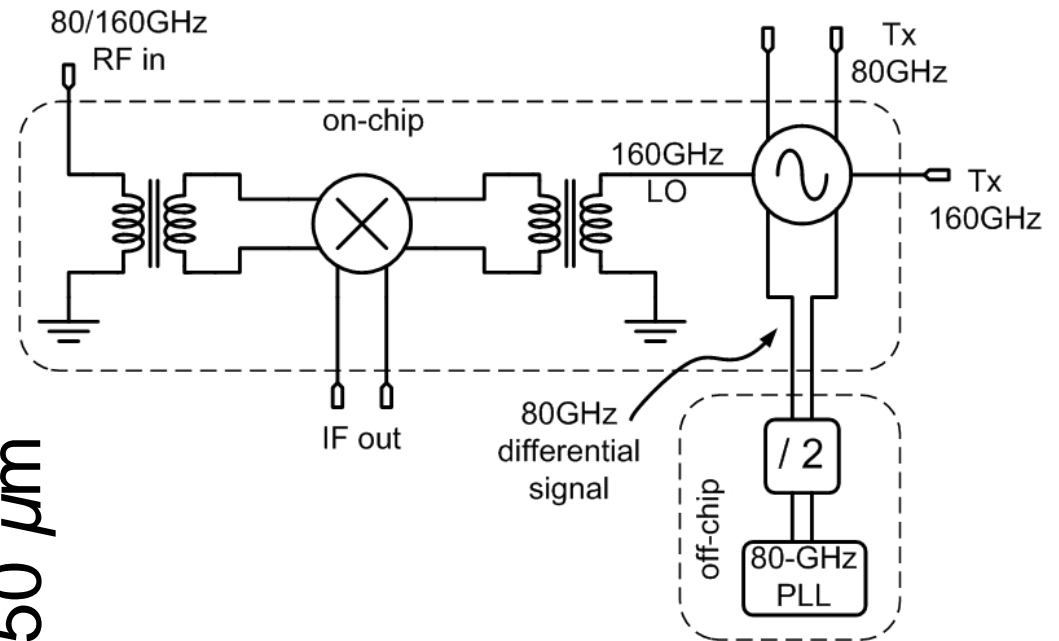
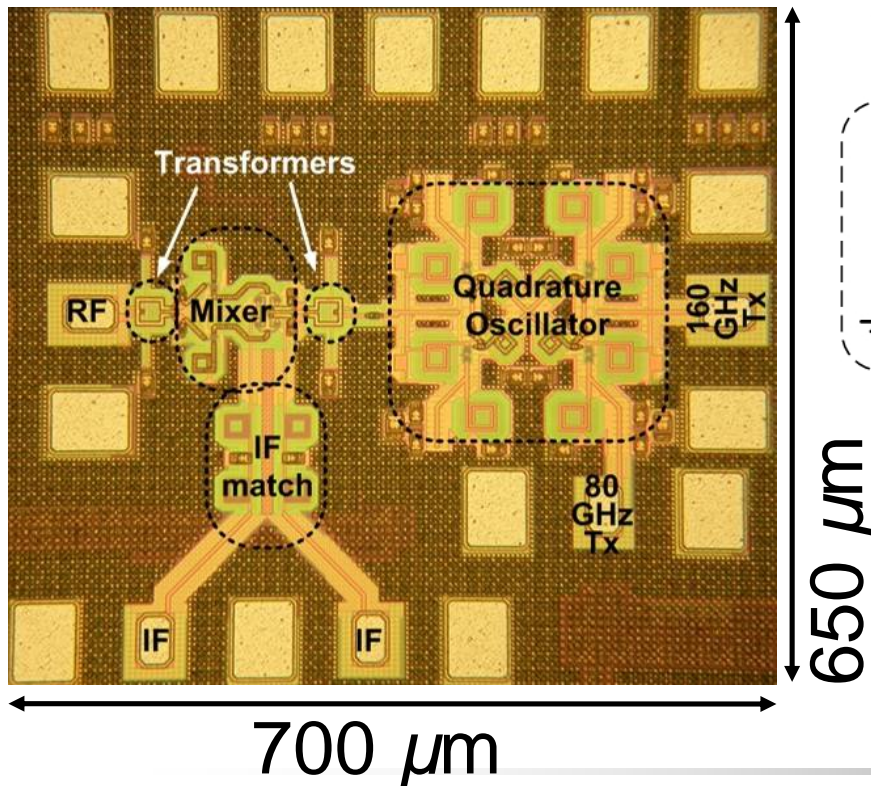
Amplifier Linearity - 130GHz





80/160-GHz Transceiver

- Transmit and receive simultaneously in 80- and 160-GHz bands

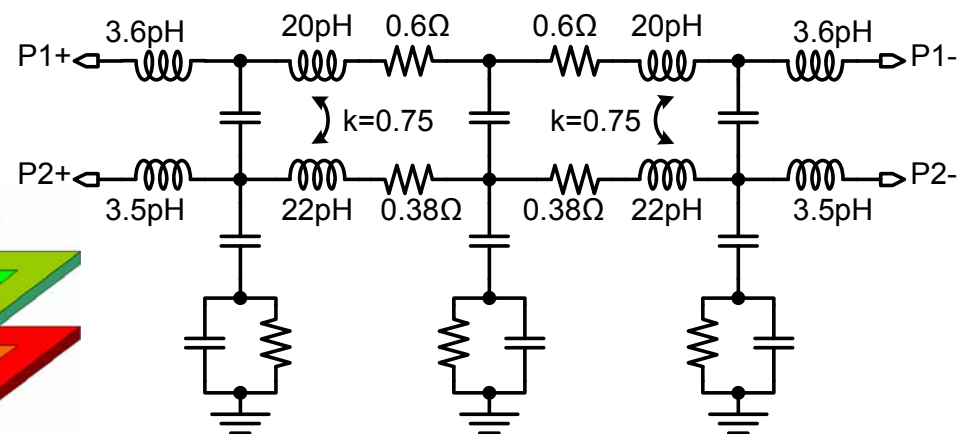
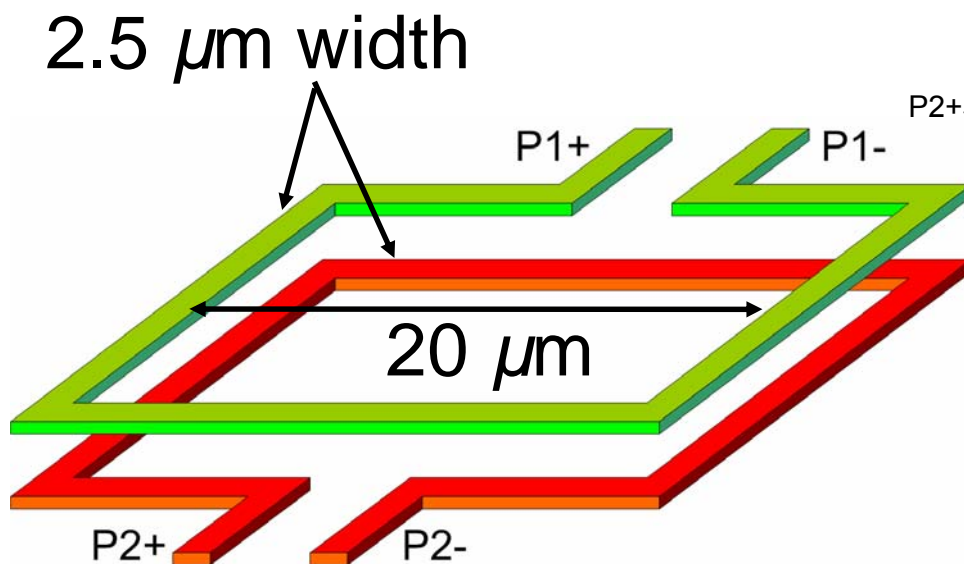


[E. Laskin et al. RFIC-07]



160-GHz Transformer

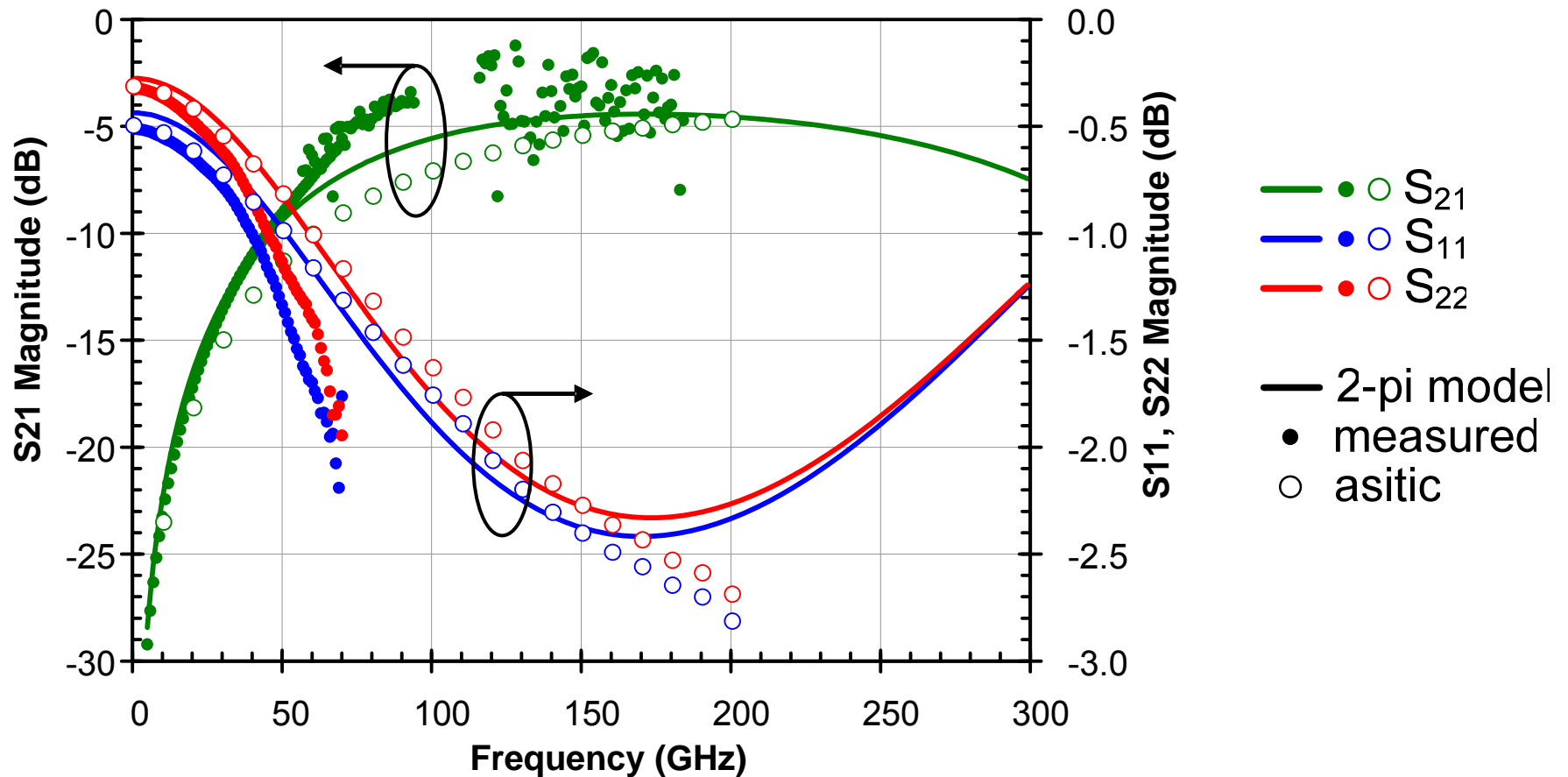
- Top 2 metal layers of a standard backend
- Optimized for lowest loss at 160 GHz
- 2-pi model includes substrate model



model from ASITIC



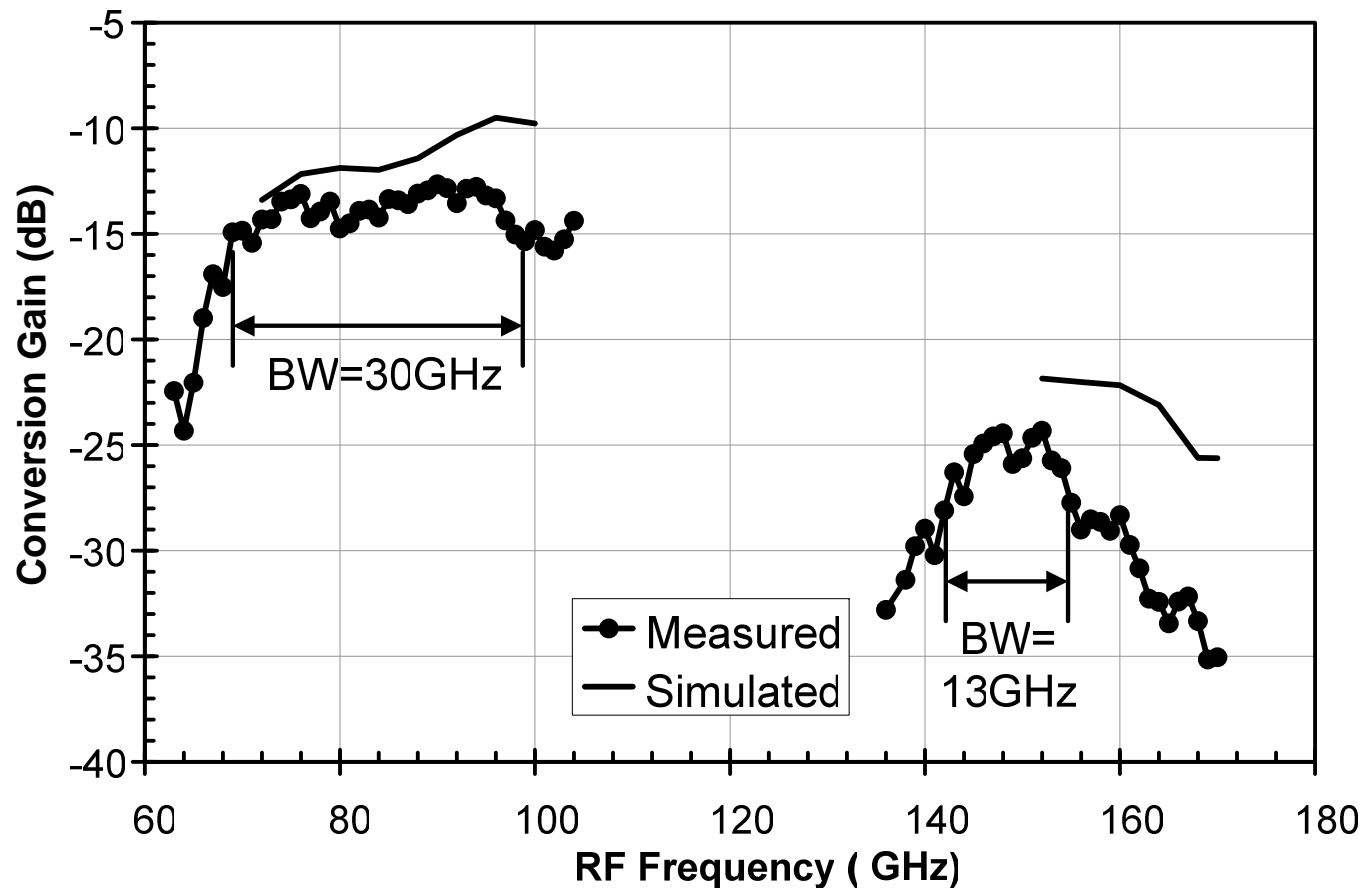
Transformer Meas. vs. Sims





80/160-GHz Transceiver

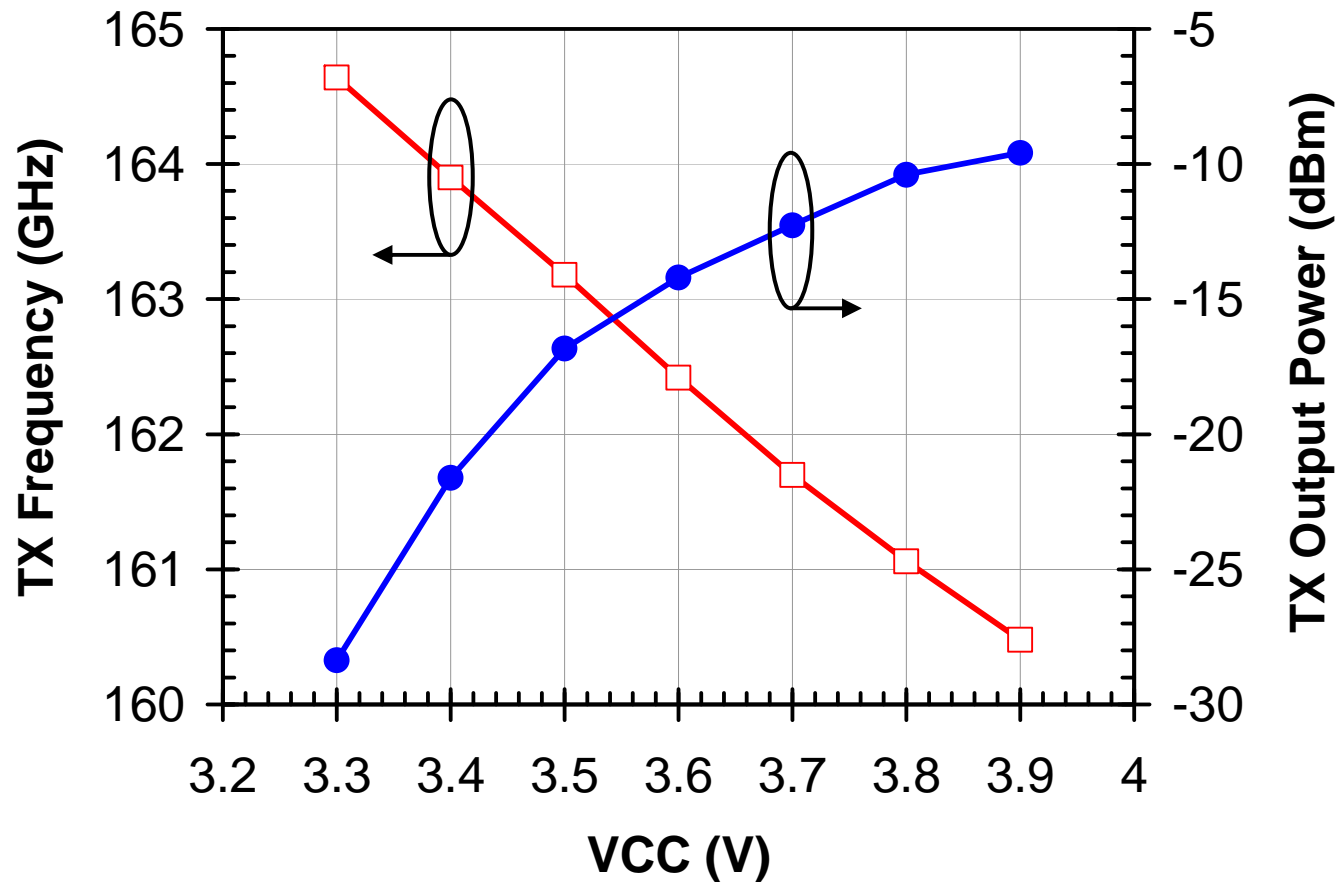
- Receiver conversion gain:





80/160-GHz Transceiver

- Single-ended TX power increases with VCC





Conclusions

- Many applications above 100GHz for CMOS/SiGe
- CMOS & SiGe devices are capable of 100+ GHz
- Circuits demonstrated at & above 100 GHz
- Integrated 80/160GHz transceiver in silicon



Acknowledgements

- CITO, NSERC for funding
- STMicroelectronics for fabrication
- ECTI, CFI, OIF for equipment
- Jaro Pristupa and CMC for CAD support